

Substitute for form 1449/PTO  <b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b>  (Use as many sheets as necessary)	Application Number	10/524,809
	Filing Date	02/15/2005
	Inventor(s)	James S. Im
	Art Unit	2895
	Examiner Name	Fernando L. Toledo
	Attorney Docket Number	070050.2721

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	11.	5620910	4/15/1997	Teramoto, Satoshi
	12.	5710050	1/20/1998	Makita, Naoki ; Miyamoto, Tadayoshi
	13.	5736709	4/7/1998	Neiheisel, Gary L.

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	15.	6117301	9/12/2000	Freudenberger, Renate ; Zielonka, Andreas
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	49.	6577380	6/10/2003	Sposili, Robert S. ; Farmiga, Nestor O. ; Jain, Kanti

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	62.	6961117	11/1/2005	Im, James S.
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	68.	7300858	11/27/2007	Im, James S.
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	72.	20020096680	7/25/2002	Sugano, Yukiyasu ; Fujino, Masahiro ; Mano, Michio ; Asano, Akihiko ; Ino, Masumitsu ; Urazono, Takenobu ; Takatoku, Makoto
	73.	20020119609	8/29/2002	Hatano, Mutsuko ; Yamaguchi, Shinya ; Kimura, Yoshinobu ; Park, Seong Kee
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	76.	20030006221	1/9/2003	Hong, Minghui ; Ye, Kaidong ; An, Chengwu ; Liu, Da Ming

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	81.	20030148565	8/7/2003	Yamanaka, Hideo
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	86.	20040182838	9/23/2004	Das, Palash, P. ; Bolliger, Bruce, E. ; Patel, Parthiv, S. ; Klene, Brian, C. ; Melcher, Paul, C. ; Saethre, Robert, B.
	87.	20040222187	11/11/2004	Lin, Kun Chih
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	89.	20050059265	3/17/2005	Im, James

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